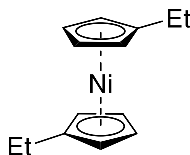
Catalog # 28-0083 Bis(ethylcyclopentadienyl)nickel, min. 98%



Thermal Behavior:

- Boiling point: 90°C

Technical Notes:

1. ALD/CVD precursor for nickel thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
NiO_x	ALD ALD PEALD	40°C - 50°C	- 0.45 Torr 0.44 Torr	O_3 *or* H_2O O_2 $^{PL}O_2$	150-300°C 200-300°C 100-325°C	1 2 3
Ni	PEALD	85°C	-	$^{PL}N_2/H_2$	200-360°C	4-5

References:

1. *J. Crystal Growth*, **2008**, *310*, 5464.
2. *Nano Lett.*, **2009**, *9*, 1476.
3. *Korean J. Chem. Eng.* **2018**, *35*, 2474.
4. *ACS Appl. Mater. Interfaces* **2017**, *9*, 24722.
5. *J. Vac. Sci. Technol. A*, **2018**, *36*, 01A119.